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... the breakdown as a result of the trapping of **positive charges** during the stress.

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some parts of the device, due to the **positive charges** trapped ... of the injected **charge**. 2. Preparation of the samples. **Oxynitride** films (9 nm thick) were ...

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Patent 4901133: Multilayer semi-insulating film for hermetic wafer ...

a layer of silicon rich **oxynitride** overlying the oxygen doped polycrystalline

... whereby fixed **positive charge** effects are eliminated and the surface ...

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Determination of effects of deposition and anneal properties for ...

Due to the hydrogen free nature of thermolysis, may form an **oxynitride** layer ...

The curves show significant bulk **positive charge** trapping during the 50 ...

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The **oxynitride**. interfacial layer (1.2nm) was formed by oxidation at 850 ...

because of exist fixed **positive charges** in interfacial layer. ...

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RPN **Oxynitride** Gate Dielectrics. for 90 nm Low Power CMOS. Applications. A. Veloso

... 37 mV ⇒ RPN oxynitrides exhibit more **positive charges** at the ...

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for 20% He-RPN **oxynitride** is. approximately 40 mV lower. This indicates that RPN.

oxynitrides exhibit more **positive charges** at the interface ...

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... with Stacked Oxide/Nitride and **Oxynitride** Gate Dielectrics Prepared by RPECVD

... During electrical stresses, **positive charges** and hole trapping are ...

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as reduced interface trapped **charge** generation resulting from. compensation effect

of inserted ... nitrogen incorporation into HfO (ie, hafnium **oxynitride**: ...
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10:00, 455, Characterization of **Oxynitride** Dielectric Films Grown in Nitric ...







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